



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

MPSA56

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

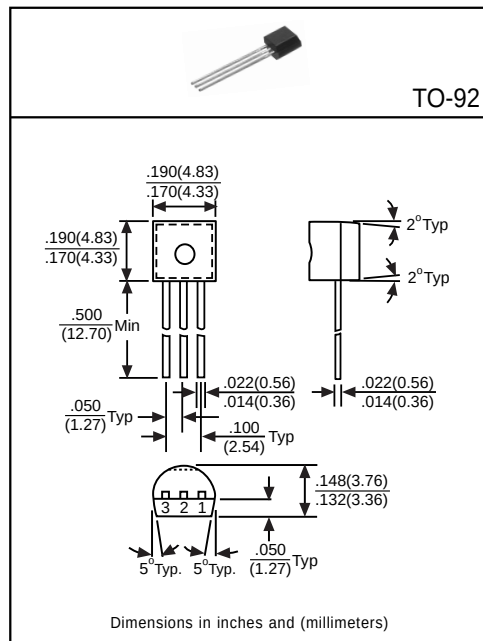
Designed for general purpose amplifier applications.

Pinning

- 1 = Emitter
- 2 = Base
- 3 = Collector

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-80	V
Collector-Emitter Voltage	V_{CE0}	-80	V
Emitter-Base Voltage	V_{EB0}	-4	V
Collector Current (DC)	I_C	-500	mA
Collector Current (pulse)	I_C	-1000	mA
Total Power Dissipation	P_D	625	mW
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}\text{C}$



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CB0}	-80	-	-	V	$I_C=-100\mu\text{A}$, $I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CE0}	-80	-	-	V	$I_C=-1\text{mA}$, $I_B=0$
Emitter-Base Breakdown Voltage	BV_{EB0}	-4	-	-	V	$I_E=-100\mu\text{A}$, $I_C=0$
Collector Cutoff Current	I_{CB0}	-	-	-0.1	μA	$V_{CB}=-80\text{V}$, $I_E=0$
	I_{CE0}	-	-	-0.1	μA	$V_{CE}=-60\text{V}$, $I_B=0$
Collector-Emitter Saturation Voltage ⁽¹⁾	$V_{CE(sat)}$	-	-	-0.25	V	$I_C=-100\text{mA}$, $I_B=-10\text{mA}$
Base-Emitter On Voltage ⁽¹⁾	$V_{BE(on)}$	-	-	-1.2	V	$I_C=-100\text{mA}$, $V_{CE}=-1\text{V}$
DC Current Gain ⁽¹⁾	h_{FE1}	50	-	-	-	$I_C=-10\text{mA}$, $V_{CE}=-1\text{V}$
	h_{FE2}	50	-	-	-	$I_C=-100\text{mA}$, $V_{CE}=-1\text{V}$
Transition Frequency	f_T	50	-	-	MHz	$I_C=-100\text{mA}$, $V_{CE}=-1\text{V}$, $f=1\text{MHz}$

(1)Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$